

IN THE CLAIMS

Please amend the claims as follows:

1. (TWICE AMENDED) A device comprising:

an outer portion comprising an electrically insulative material, having (i) dimensions effective to prevent or inhibit plasma arcing to an electrically conductive surface of a plasma processing chamber aperture and (ii) a flange section configured to remain outside of said plasma processing chamber aperture ; and

an inner opening, completely surrounded by the electrically insulative material of the outer portion, having dimensions effective to enable transmission of a physical signal, 10 a gas, a gas mixture or other material through the device.

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2. A plasma processing chamber having:

at least one aperture therein, the at least one aperture having an exposed electrically conductive surface, and
the device of Claim 1, located inside the aperture.

3. A method of making a plasma processing chamber, the

chamber having at least one aperture therein, the at least one aperture having an exposed electrically conductive surface, the method comprising inserting the device of Claim 1 into the 5 aperture.

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4. A method of processing a workpiece, comprising the following steps:

(A) exposing the workpiece to a plasma in the chamber of

10 Claim 2; and

(B) transmitting a physical signal or a gas, gas mixture or other material through the device into or out from the chamber.

5. (TWICE AMENDED) A plasma processing chamber having:
at least one aperture therein, the at least one aperture having an exposed electrically conductive surface, and

a device inside the aperture, the device comprising an electrically insulative material and having

(i) dimensions effective to prevent or inhibit plasma arcing to the exposed electrically conductive surface of the aperture, wherein a flange section of said device is configured to remain outside said aperture ; and

(ii) an inner opening completely surrounded by the electrically insulative material, the inner opening having dimensions effective to enable transmission of a physical signal, a gas, a gas mixture or other material through the device.

6. (TWICE AMENDED) A method of making a plasma processing chamber, the chamber having at least one aperture therein, the at least one aperture having an exposed electrically

conductive surface, the method comprising inserting a device into
5 the aperture, the device comprising an electrically insulative
material and having:

dimensions effective to prevent or inhibit plasma arcing
to the exposed electrically conductive surface of the aperture,
wherein a flange section of said device is configured to remain
outside said aperture ; and

an inner opening completely surrounded by the
electrically insulative material, the inner opening having
dimensions effective to enable transmission of a physical signal,
a gas, a gas mixture or other material through the device.

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7. The method of Claim 6, further comprising, prior to
said inserting, the step of forming said aperture in said chamber.

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8. (TWICE AMENDED) A method of processing a workpiece,
comprising:

exposing the workpiece to a plasma in a chamber, the
chamber having at least one aperture therein, the at least one
5 aperture having

- 1) an exposed electrically conductive surface; and
2) a device in the aperture, the device comprising
an electrically insulative material and having

10 (i) dimensions effective to prevent or inhibit plasma arcing to the exposed electrically conductive surface of the aperture, wherein a flange section of said device is configured to remain outside said aperture, and

(ii) an inner opening completely surrounded by the electrically insulative material, the inner opening having dimensions effective to enable transmission of a physical signal, a gas, a gas mixture or other material through the device; and

(iii) transmitting a physical signal, a gas, a gas mixture or other material through the device into or out from the chamber.

9. A method of operating a plasma processing chamber, wherein the chamber has at least one aperture therein and the aperture has an exposed electrically conductive surface, the method comprising the steps of:

10. The method of Claim 9, wherein said plasma exists in
said chamber for a predetermined period of time

11. (AMENDED) The method of Claim 9, further comprising, prior to step B, the steps of:

exposing a workpiece to the plasma, and
transmitting a physical signal, a gas, a gas mixture or
other material through the device into or out from the chamber.

12. (AMENDED) The device according to claim 1, further comprising:

a lower section having a first width effective to fit the
plasma processing chamber aperture within a predefined tolerance;
and

said flange section having a second width that is
greater than a corresponding width of said plasma processing
chamber aperture.

13. (AMENDED) The device according to claim 12, wherein
said device is held in said plasma processing chamber aperture via
a wire loop configured to hold said device under typical plasma
processing conditions.

14. (AMENDED) The device according to claim 12, wherein
said lower section has a first length and said flange section has
a second length.

15. The device according to claim 14, wherein said first length is greater than or equal to a length of a channel section of said plasma processing chamber aperture.

16. The device according to claim 1, wherein an end of said device has an angle, said angle measured with reference to a bottom of said device.

17. The device according to claim 16, wherein said angle is non-orthogonal.

18. The device according to claim 1, wherein said physical signal comprises a spectroscopic endpoint detection signal.

19. The plasma processing chamber of claim 2, wherein said at least one aperture comprises an endpoint detection channel.

20. The device according to claim 1, wherein the electrically insulative material is selected from the group consisting of ceramics, multi-crystal ceramics, polyvinyl polymers, polytetrafluoroethylene, polyethylene, polypropylene, polyimides, polycarbonates and single crystal insulative minerals.